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74HC253; 74HCT253

Dual 4-input multiplexer; 3-state Rev. 5 — 21 January 2015

Product data sheet

General description 1.

The 74HC253; 74HCT253 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC253; 74HCT253 provides a dual 4-input multiplexer with 3-state outputs which selects 2 bits of data from up to four sources selected by common data select inputs (S0, S1). The two 4-input multiplexer circuits have individual active LOW output enable inputs (1OE, 2OE).

The 74HC253 and 74HCT253 are the logic implementation of a 2-pole, 4-position switch, where the position of the switch is determined by the logic levels applied to S0 and S1. The outputs are forced to a high-impedance OFF-state when nOE is HIGH.

The logic equations for the outputs are:

$$1Y = 1\overline{OE} \bullet (1I0 \bullet \overline{SI} \bullet \overline{SO} + 1I1 \bullet \overline{SI} \bullet SO + 1I2 \bullet S1 \bullet \overline{SO} + 1I3 \bullet S1 \bullet SO)$$
$$2Y = 2\overline{OE} \bullet (2I0 \bullet \overline{SI} \bullet \overline{SO} + 2I1 \bullet \overline{SI} \bullet SO + 2I2 \bullet S1 \bullet \overline{SO} + 2I3 \bullet S1 \bullet SO)$$

2. Features and benefits

- Non-inverting data path
- 3-state outputs interface directly with system bus
- Complies with JEDEC standard no. 7A
- Common select inputs
- Separate output enable inputs
- Input levels:
 - ◆ For 74HC253: CMOS level
 - ◆ For 74HCT253: TTL level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from −40 °C to +85 °C and from −40 °C to +125 °C



3. Applications

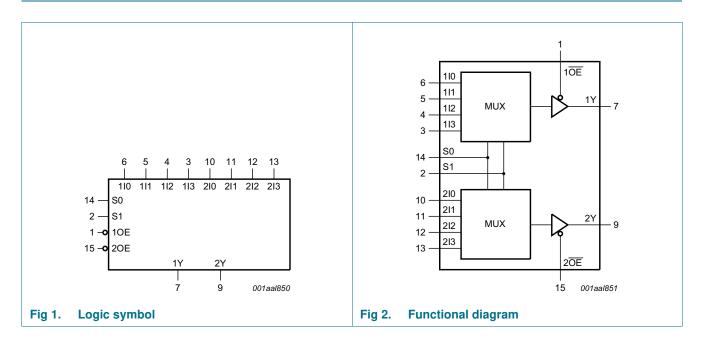
- Data selectors
- Data multiplexers

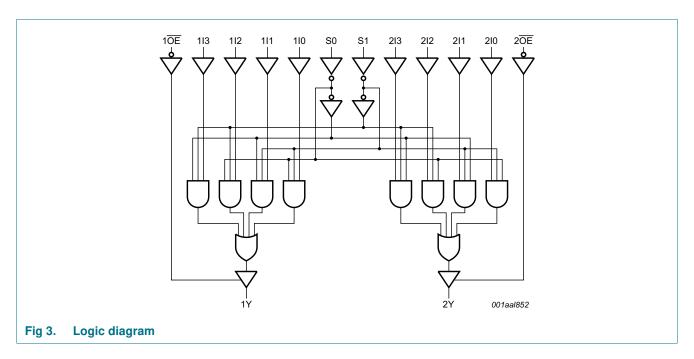
4. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74HC253N	-40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4						
74HCT253N	-									
74HC253D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1						
74HCT253D	-		3.9 mm							
74HC253DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1						
74HCT253DB	-		body width 5.3 mm							

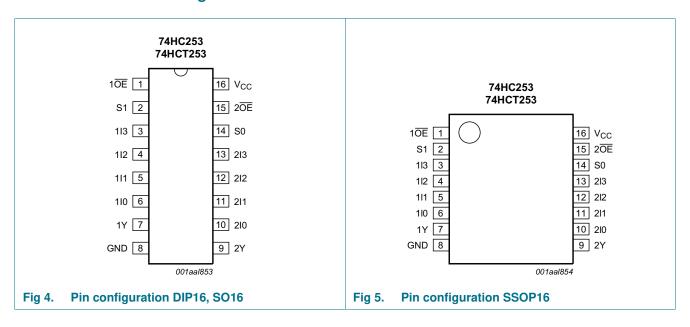
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description			
10E, 20E	1, 15	output enable inputs (active LOW)			
S0, S1	14, 2	data select inputs			
110, 111, 112, 113	6, 5, 4, 3	data inputs source 1			
1Y	7	multiplexer output source 1			
GND	8	ground (0 V)			
2Y	9	multiplexer output source 2			
210, 211, 212, 213	10, 11, 12, 13	data inputs source 2			
V _{CC}	16	supply voltage			

7. Functional description

Table 3. Function table[1]

select Inputs	select Inputs data inpu					output enable	output
S0	S1	nI0	nl1	nl2	nl3	nOE	nY
X	X	Х	Х	Х	Х	Н	Z
L	L	L	Х	Х	Х	L	L
L	L	Н	Х	Х	Х	L	Н
Н	L	X	L	Х	Х	L	L
Н	L	X	Н	Х	Х	L	Н
L	Н	X	Х	L	Х	L	L
L	Н	X	Х	Н	Х	L	Н
Н	Н	Х	Х	Х	L	L	L
Н	Н	X	X	X	Н	L	Н

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	-	±50	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		- 65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$				
		DIP16 package	[2]	-	750	mW
		SO16 package	[3]	-	500	mW
		SSOP16 package	[4]	-	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- [2] P_{tot} derates linearly with 12 mW/K above 70 °C.
- [3] P_{tot} derates linearly with 8 mW/K above 70 °C.
- [4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Conditions 74HC253		7	4HCT25	3	Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C −40 °C			+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC253	3									
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_O = -20 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	٧
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	٧
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	٧
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μА
loz	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL};$ $V_{O} = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	±0.5	-	±5.0	-	±10.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-					pF
74HCT2	53							I .		
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_O = -6 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	٧
		$I_{O} = 6.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	٧
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
OZ	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	±0.5	-	±5.0	-	±10	μА
I _{cc}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μΑ

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C to	+85 °C	-40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
Δl _{CC}	additional supply current	$V_I = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $I_O = 0 \text{ A}$								
		per input pin; 1ln, 2ln inputs	-	40	144	-	180	-	196	μА
		per input pin; nOE input	-	110	396	-	495	-	539	μΑ
		per input pin; Sn input	-	110	396	-	495	-	539	μΑ
Cı	input capacitance		-	3.5	-					рF

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 8.

Symbol	Parameter	Conditions	25	°C	-40 °C to +85 °C	-40 °C to +125 °C	Unit
			Тур	Max	Max	Max	
74HC253	3						'
t _{pd}	propagation delay	1In to 1Y or 2In to 2Y; see Figure 6					
		V _{CC} = 2.0 V	55	175	220	265	ns
		V _{CC} = 4.5 V	20	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	17	-	-	-	ns
		V _{CC} = 6.0 V	16	30	37	45	ns
		Sn to nY; see Figure 6					
		V _{CC} = 2.0 V	58	175	220	265	ns
		V _{CC} = 4.5 V	21	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	18	-	-	-	ns
		V _{CC} = 6.0 V	17	30	37	45	ns
t _{en}	enable time	nOE to nY; see Figure 7 [2]					
		V _{CC} = 2.0 V	30	100	125	150	ns
		V _{CC} = 4.5 V	11	20	25	30	ns
		V _{CC} = 6.0 V	9	17	21	26	ns
t _{dis}	disable time	nOE to nY; see Figure 7 [3]					
		V _{CC} = 2.0 V	41	150	190	225	ns
		V _{CC} = 4.5 V	15	30	38	45	ns
		V _{CC} = 6.0 V	12	26	33	38	ns
t _t	transition time	see Figure 6 [4]					
		V _{CC} = 2.0 V	14	60	75	90	ns
		V _{CC} = 4.5 V	5	12	15	18	ns
		V _{CC} = 6.0 V	4	10	13	15	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 8.

Symbol	Parameter	Conditions		25	°C	-40 °C to +85 °C	-40 °C to +125 °C	Unit
				Тур	Max	Max	Max	
C _{PD}	power dissipation capacitance	per multiplexer; V _I = GND to V _{CC}	[5]	55	-			pF
74HCT25	53		·					-
t _{pd}	propagation delay	1ln to 1Y or 2ln to 2Y; see Figure 6	[1]					
		V _{CC} = 4.5 V		20	38	48	57	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		17	-	-		ns
		Sn to nY; see Figure 6						
		V _{CC} = 4.5 V		22	40	50	60	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		19	-			ns
t _{en}	enable time	nOE to nY; V _{CC} = 4.5 V; see Figure 7	[2]	14	30	38	45	ns
t _{dis}	disable time	$\overline{\text{OE}}$ to nY; $V_{\text{CC}} = 4.5 \text{ V}$; see Figure 7	[3]	13	30	38	45	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6		5	12	15	18	ns
C _{PD}	power dissipation capacitance	per multiplexer; V _I = GND to V _{CC} – 1.5 V	[5]	55	-			pF

- [1] t_{pd} is the same as t_{PHL} , t_{PLH} .
- [2] t_{en} is the same as t_{PZH} , t_{PZL} .
- [3] t_{dis} is the same as t_{PHZ} , t_{PLZ} .
- [4] t_t is the same as t_{THL} , t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

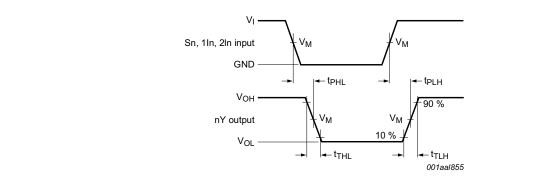
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = sum \text{ of outputs.}$

12. Waveforms



Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delays input (Sn, 1ln, 2ln) to output (nY) and output (nY) transition times

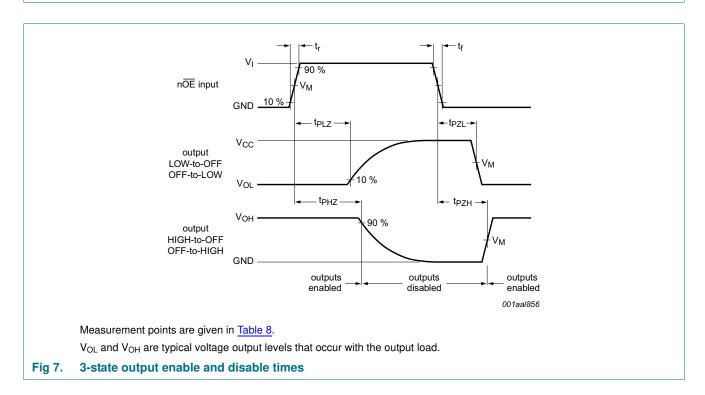
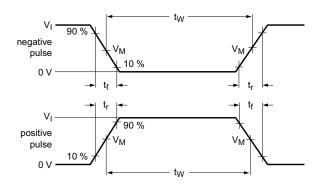
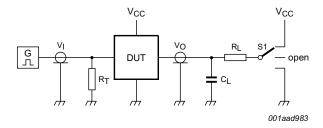


Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74HC253	0.5V _{CC}	0.5V _{CC}
74HCT253	1.3 V	1.3 V





Measurement points are given in Table 8 and test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_L = Load resistor.

Fig 8. Test circuit for measuring switching times

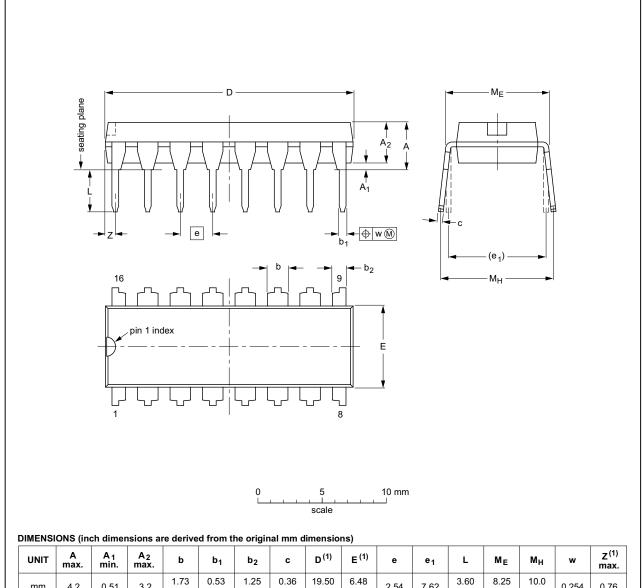
Table 9. Test data

Туре	Input		Load		Switch position			
	V _I	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74HC253	V _{CC}	6 ns	50 pF	1 kΩ	open	GND	V _{CC}	
74HCT253	3 V	6 ns	50 pF	1 kΩ	open	GND	V _{CC}	

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT38-4						95-01-14 03-02-13	

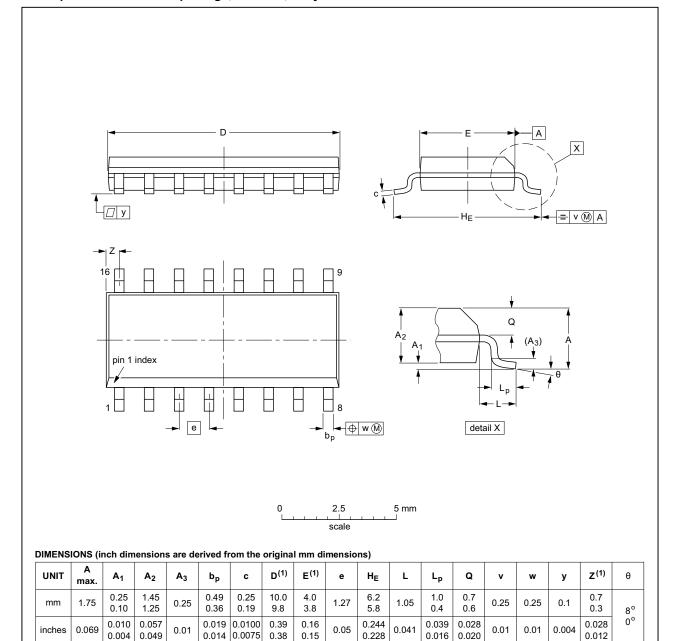
Fig 9. Package outline SOT38-4 (DIP16)

74HC_HCT253

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SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

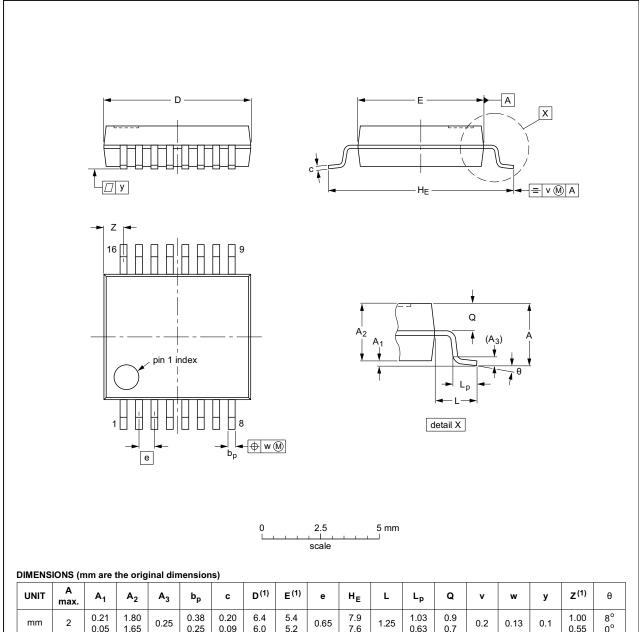
Fig 10. Package outline SOT109-1 (SO16)

74HC_HCT253

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	C	D ⁽¹⁾	E ⁽¹⁾	e	HE	L	Lp	Q	٧	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		ISSUE DATE	
SOT338-1		MO-150				99-12-27 03-02-19

Fig 11. Package outline SOT338-1 (SSOP16)

74HC_HCT253

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT253 v.5	20150121	Product data sheet	-	74HC_HCT253 v.4
Modifications:	• <u>Table 7</u> : Power di	ssipation capacitance cor	ndition for 74HCT253 i	s corrected.
74HC_HCT253 v.4	20111212	Product data sheet	-	74HC_HCT253 v.3
Modifications:	Legal pages upda	ated.		
74HC_HCT253 v.3	20100422	Product data sheet	-	74HC_HCT253_CNV v.2
74HC_HCT253_CNV v.2	970828	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Dual 4-input multiplexer; 3-state

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